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AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-11 (canceled)

Claim 12 (currently amended): The method according to claim ~~16~~20, wherein the first metallic thin film and the second metallic thin film are formed on the piezoelectric plate via sputtering.

Claim 13 (currently amended): The method according to claim ~~16~~20, wherein the first metallic thin film and the second metallic thin film are formed on the piezoelectric plate via vapor deposition.

Claim 14 (currently amended): The method according to claim ~~16~~20, wherein the first metallic thin film is formed to have a bi-layer structure of a lower tungsten thin film and an upper titanium thin film.

Claim 15 (original): The method according to claim 14, wherein the second metallic thin film is formed on the upper titanium thin film and further comprising the step of converting the second metallic thin film into α -tantalum.

Claim 16 (canceled)

Claim 17 (currently amended): The method according to claim ~~16~~20, wherein the first metallic thin film includes a laminated metallic film formed by a plurality of metallic

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thin films, and the at least one portion of the first metallic thin film at a side of the laminated metallic film where the second metallic thin film is laminated includes titanium.

Claim 18 (previously presented): The method according to claim 17, wherein the first metallic thin film other than the first metallic thin film laminated with the second metallic thin film of the laminated metallic thin film includes a metal containing Au, α -tantalum, β -tantalum, W, Ag, Mo, Cu, Ni, Fe, Cr or Zr as a principal component.

Claim 19 (currently amended): The method according to claim ~~16~~20, wherein a thickness of the first metallic thin film is formed to be about 3 nm or more.

Claim 20 (currently amended): ~~The method according to claim 16,~~
wherein A method for manufacturing a surface acoustic wave device comprising:
providing a piezoelectric plate;
forming a first metallic thin film on the piezoelectric plate; and
forming a second metallic thin film on the first metallic thin film, the second
metallic film including tantalum as a principal component and at least one portion of the
tantalum of the second metallic thin film is α -tantalum; wherein
at least one portion of the first metallic thin film includes titanium; and
the surface acoustic wave device is arranged to utilize shear horizontal waves.